

Prepared	<i>Ching</i>	Product Specifications AN7161N		
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Approved	<i>Ching</i>			

Structure	Silicon Monolithic Bipolar IC
Appearance	SIL-12 Pin Plastic Package (Power Type with Fin attached)
Application	Hi-Fi and Car Stereo
Function	BTL 23W Audio Power Amplifier

A	Absolute Maximum Ratings				
No.	Item	Symbol	Ratings	Unit	Note
1	Storage Temperature	Tstg	-55 ~ +150	° C	1
2	Operating Ambient Temperature	Topr	-30 ~ +75	° C	1
3	Supply Voltage	Vcc	26	V	
4	Supply Current	Icc	4.0	A	
5	Power Dissipation	P _D	62.5	W	
6	Surge Voltage	V _{surge}	50	V	

Note: 1) The temperature of all items shall be Ta=25°C except storage temperature and operating ambient temperature.

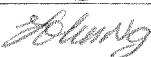


Eff. Date	Eff. Date	Eff. Date	Eff. Date	
12-DEC-95	11-JUL-98			

Prepared		Product Specifications AN7161N	Ref. No.	B-1
Checked			Total Page	7
Approved			Page No.	2

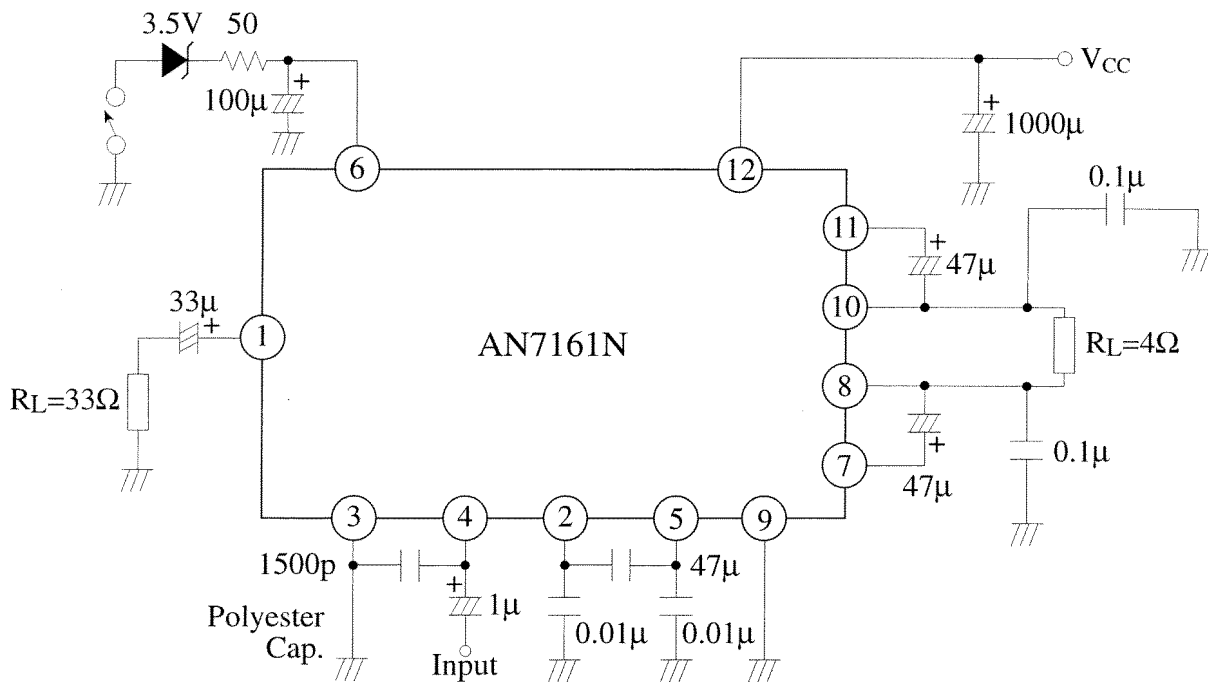
B Electrical Characteristics (Unless otherwise specified, the ambient temperature is 25°C ± 2°C)									
No	Item	Symbol	Test Circuit	Conditions	Limits			Unit	Note
					min	typ	max		
1	Quiescent Circuit Current	I _{CQ}	1	V _{CC} =15V, V _{in} =0V	-	45	75	mA	
Power Amplifier (V _{CC} =15V, R _L =4Ω, freq.=1kHz)									
2	Output Noise Voltage	V _N	1	f=15Hz ~ 30kHz, 12dB/oct, R _g =10kΩ	-	0.6	1.0	mV	
3	Voltage Gain	G _V	1	V _{in} =5mV	48.5	50.5	52.5	dB	
4	Total Harmonic Distortion	THD	1	V _{in} =5mV	-	0.15	0.5	%	
5	Maximum Power Output	P _O	1	THD=10%	20	23	-	W	
6	Output Offset Voltage	V _{OS}	1	R _g =0Ω	-	-	150	mV	
Headphone Amplifier (V _{CC} =15V, R _L =33Ω, freq.=1kHz)									
7	Output Noise Voltage	V _{N-H}	1	f=15Hz ~ 30kHz, 12dB/oct, R _g =10kΩ	-	0.1	0.7	mV	
8	Voltage Gain	G _{V-H}	1	V _{in} =10mV Power Amplifier mute	17.5	19.5	21.5	dB	
9	Maximum Output Power	P _{O-H}	1	THD=1% Power Amplifier mute	10	-	-	mW	

Eff. Date	Eff. Date	Eff. Date	Eff. Date	
12-DEC-95	11-JUL-98			

Prepared		Product Specifications AN7161N	Ref No.	CS
Checked			Total Page	7
Approved			Page No.	3

(Description of test circuit and test method)

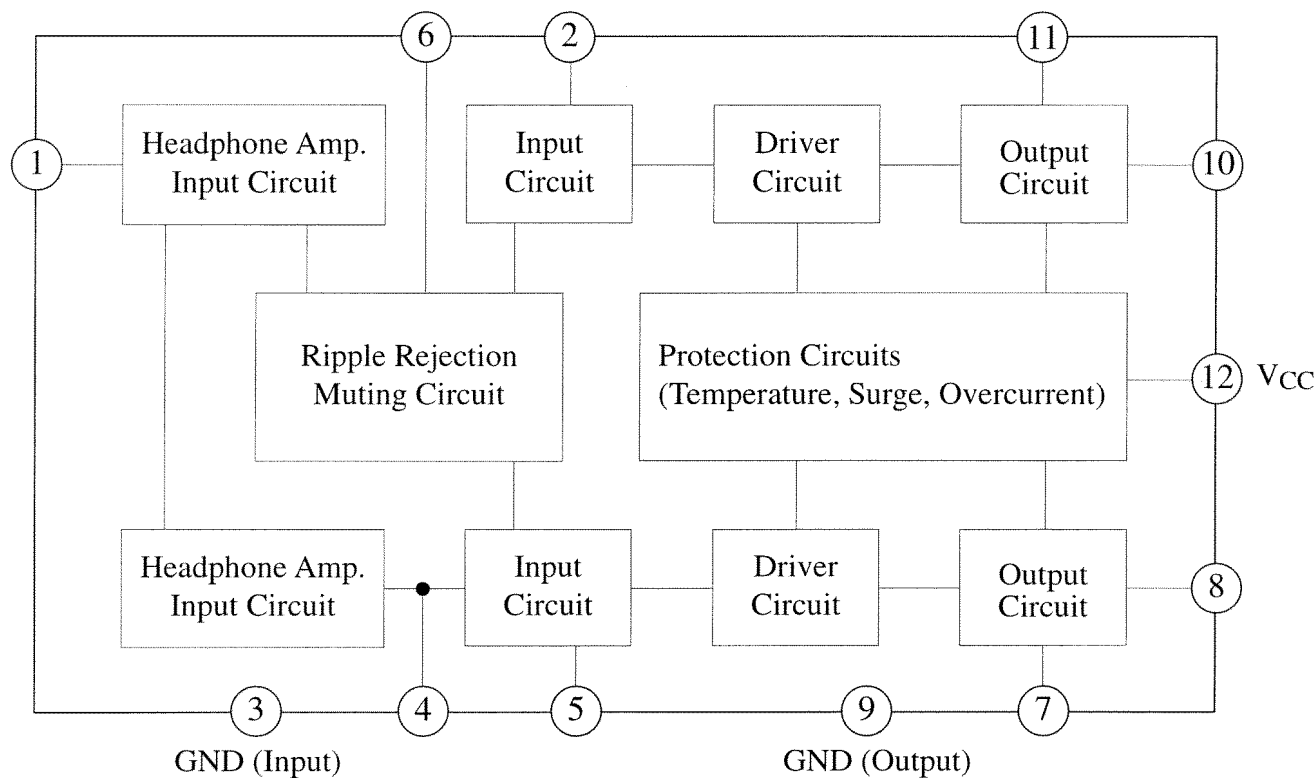
Test Circuit 1



Eff. Date	Eff. Date	Eff. Date	Eff. Date
12-DEC-95	11-JUL-98		

Prepared		Product Specifications AN7161N	Rev. No.	D-1
Checked			Total Page	7
Approved			Page No.	4

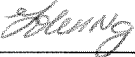
Circuit Function Block Diagram



Pin Descriptions

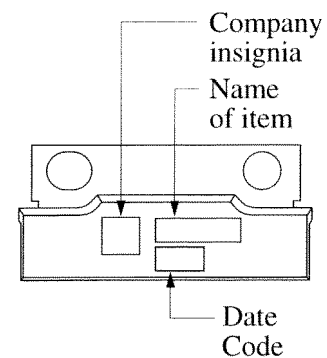
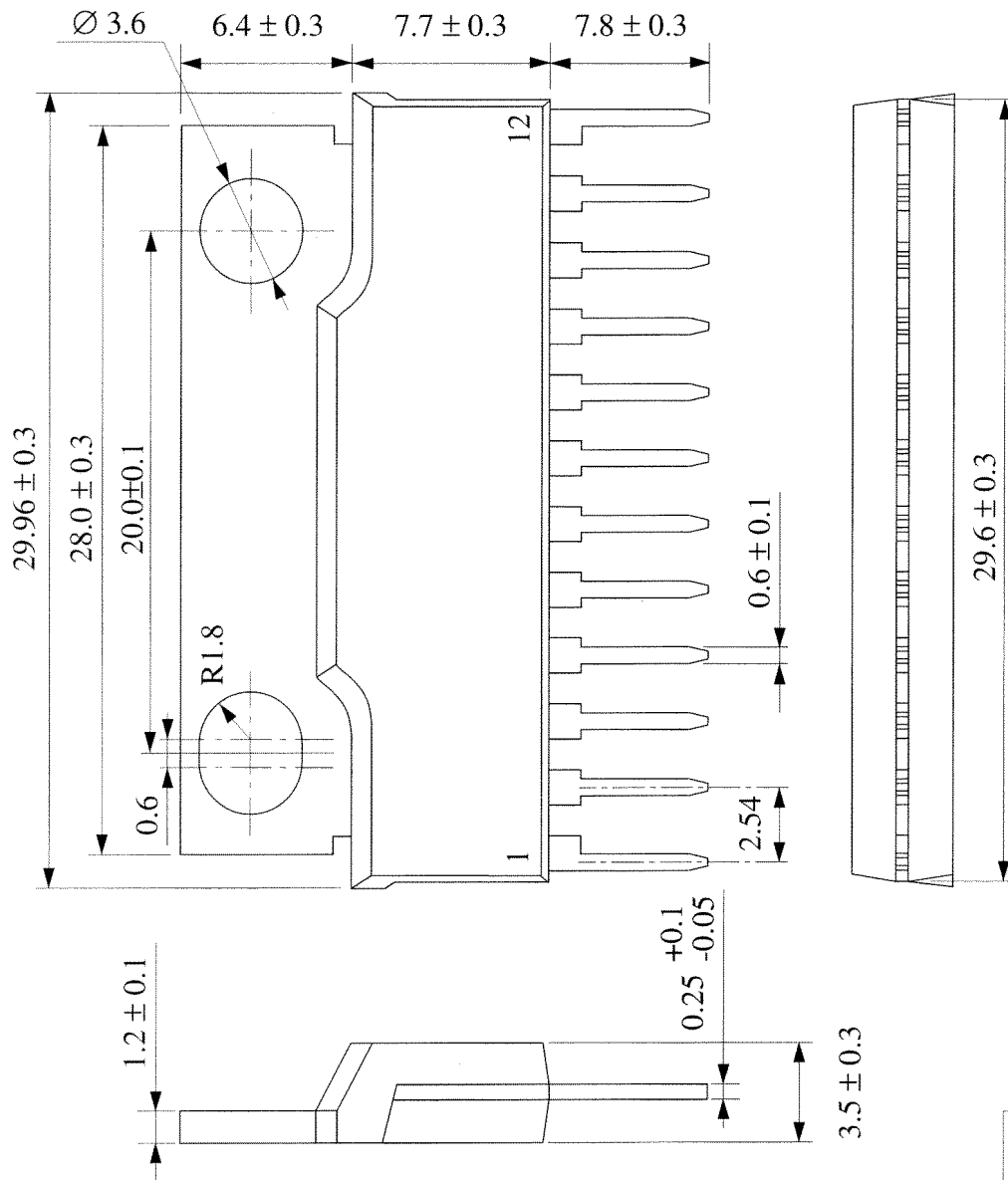
Pin No.	Description	Pin No.	Description
1	Output (Headphone)	7	Bootstrap Channel 1
2	Negative Feedback Channel 2	8	Output Channel 1
3	GND (Input)	9	GND (Output)
4	Input	10	Output Channel 2
5	Negative Feedback Channel 1	11	Bootstrap Channel 2
6	Ripple Filter	12	VCC

Eff. Date	Eff. Date	Eff. Date	Eff. Date	
12-DEC-95	11-JUL-98			

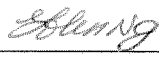
Prepared		Product Specifications AN7161N	Ref. No.	E
Checked			Total Page	7
Approved			Page No.	5

Package Name	FP-12S
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Unit : mm

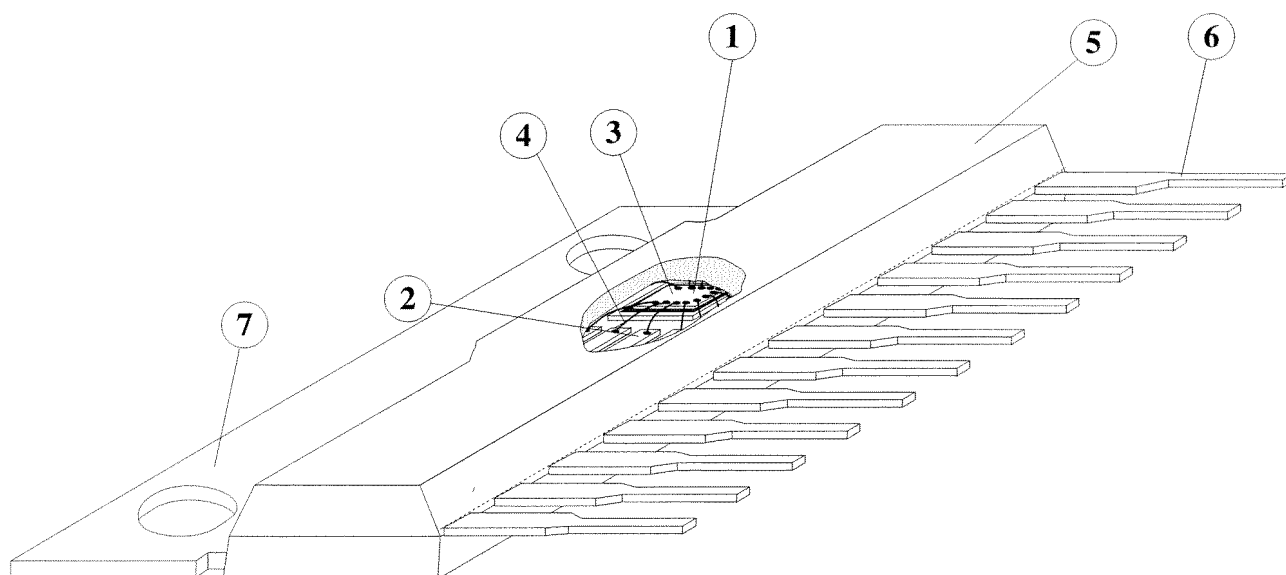


Eff. Date	Eff. Date	Eff. Date	Eff. Date
12-DEC-95	11-JUL-98		

Prepared		Product Specifications AN7161N	Ref No.	
Checked			Total Page	7
Approved			Page No.	6

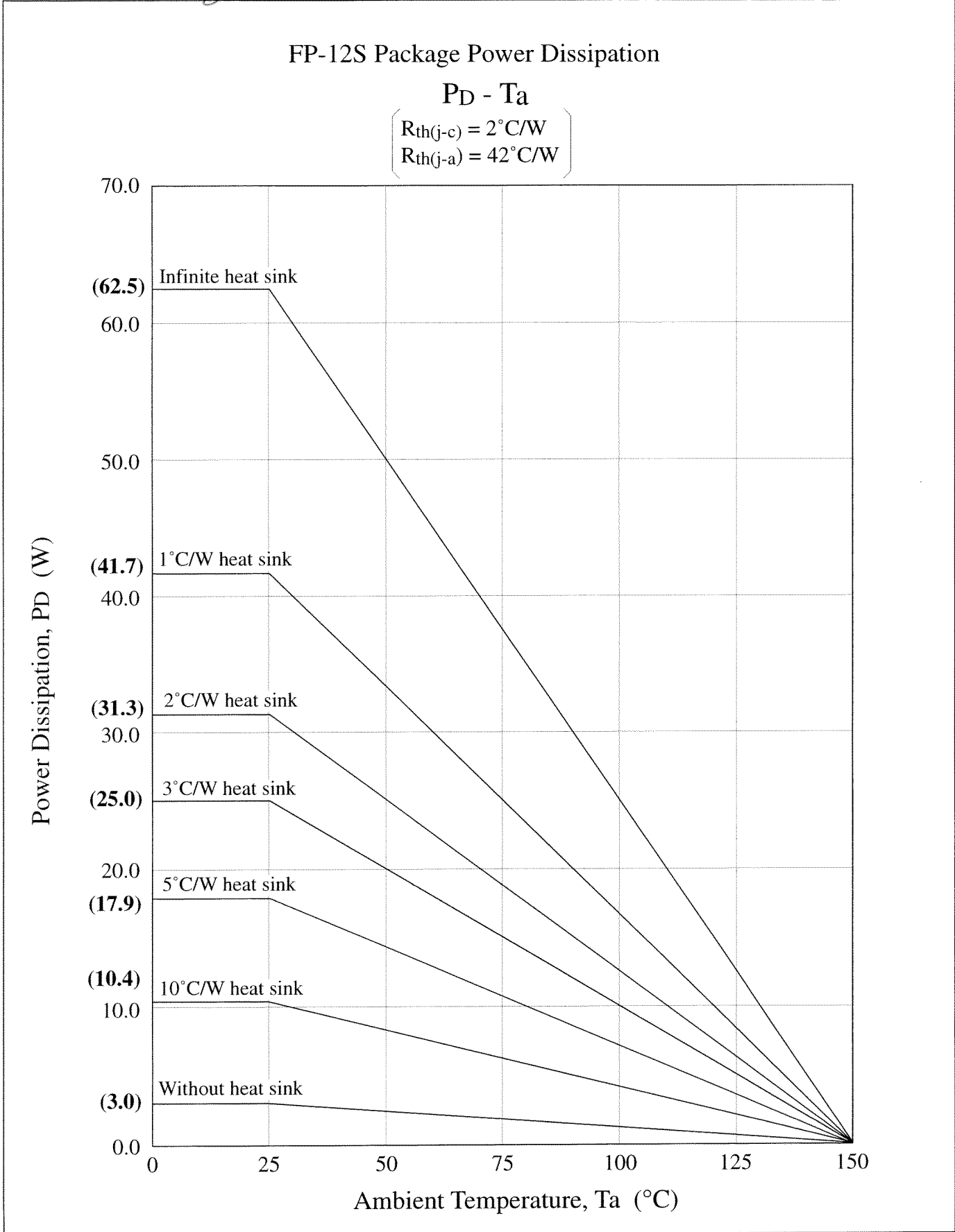
(Structure Description)

Chip surface passivation	SiN,	PSG,	Others ()	①
Lead frame material	Fe group,	Cu group,	Others ()	②, ⑥
Inner lead surface process	Ag plating,	Au plating,	Others ()	②
Outer lead surface process	Solder plating,	Solder dip,	Others ()	⑥
Chip mounting method	Ag paste,	Au-Si alloy,	Solder, Others ()	③
Wire bonding method	Thermalsonic bonding,		Others ()	④
Wire material, Diameter	Au,	Diameter 50 μm	Others ()	④
Mold material	Epoxy,		Others ()	⑤
Molding method	Transfer mold,	Multiplunger mold,	Others ()	⑤
Fin material	Cu Group		Others ()	⑦

Package FP-12S

Eff. Date	Eff. Date	Eff. Date	Eff. Date	
12-DEC-95	11-JUL-98			

Prepared		Product Specifications (Technical Data) AN7161N	Ref No.	G-1
Checked			Total Page	7
Approved			Page No.	7



Eff. Date	Eff. Date	Eff. Date	Eff. Date	
12-DEC-95	11-JUL-98			